

Index

- 0.07-NA EUV imaging system, 29
 - 0.08-NA Schwarzschild imaging, 15
 - 0.0825 NA_{mask}, 241
 - 0.25 NA, 2, 25, 603
 - 0.33 NA, 229, 237, 242, 248–253, 295, 447, 599–600, 603, 605, 609–610, 616
 - 0.45 NA, 2, 242, 248, 266, 473
 - 0.5-NA six-aspherical-mirror imaging system, 27
 - 0.50-NA ring-field imaging system, 28
 - 0.5 NA MET, 232
 - 0.5 σ , 232
 - 0.55 σ , 266
 - 0.55 NA, 251–253, 600, 603, 610, 616, 618–619, 655
 - 0.7 σ , 652
 - 2-butanone, 540
 - 2 tert-butoxycarbonyl (tBOC)-protected functional groups, 524
 - 2,2,2-trifluoroethyl *a*-chloroacrylate (EBR-9), 37
 - 2D disk, 383
 - 2D PSD of the surface topography (*PSD*_{2D}), 31, 274, 282, 285, 288, 293
 - 3D EUV mask effects, 314, 412, 429, 461, 473, 611, 614, 615, 621
 - 3D spherical target, 135
 - 4X reduction, 241
 - 5X reduction, 16
 - 10X-II Schwarzschild, 15
 - 10X reduction microstepper, 67
 - 20X reduction Schwarzschild optics, 19
- A**
- Abbe, Ernst, 26, 598
 - aberration correction, 25–26
 - ABRIXAS mission, 259
 - absolute figure uncertainty, 28
 - absorbance *A*, 500–501
 - absorbed power density, 270
 - absorber-over-layer reflection masks, 19
 - absorber patterning 35, 91, 102
 - absorber shadowing, 247, 249
 - absorber thickness, 247, 429, 444, 459, 468
 - absorption coefficient, 37
 - of PMMA, 24
 - absorption data, 690
 - absorption edge of C, 7, 351
 - absorption edge of Si, 5, 33, 37
 - acceptance testing procedure (ATP), 316
 - acetal blocking groups, 520
 - acetal protecting groups, 521
 - acid amplifier (AA), 526
 - 3BH, 527
 - acid-catalyzed deblocking, 520
 - acid-catalyzed crosslinking, 523
 - acid quantum yield, 512, 513
 - acid-sensitive dye (Coumarin-6), 509, 511
 - acrylate polymer, 521

- actinic blank inspection (ABI), 421, 433–435
- actinic wavefront metrology, 39, 625
- action requirement (AR), 66
- actuators, 105, 131, 626, 627
- acyclic-fluorine-containing monomer, 522
- aerial image 112, 246, 249, 449, 661
- contrast, 35, 429, 462, 520, 597, 610, 612, 628, 654, 645, 680
 - LER PSD, 661
 - metrology, 230, 233
 - microscope, 311
 - modeling, 653, 660, 669
 - PSD, 661
 - scanner, 309, 310
 - shape, 561
 - simulation, 441, 669
 - slope, 673
- Aerial Image Measurement System (AIMS™), 227, 308
- typical use, 310
- AES, 68
- Airy disk, 289
- Airy function $PSF_0(r)$, 289
- aliphatic esters, 502
- Alpha Demo Tool (ADT), 228, 232
- metrology, 233, 565, 606, 608
- alternating phase shift mask, 461, 470
- modified, 461
- ambient hydrocarbons, 345
- AMD Typhoon, 233
- amorphous-titanium-doped fused silica, 275
- amplified spontaneous emission (ASE), 177
- amplified spontaneous emission (ASE), back-propagating, 176
- amplitude defect, 433
- repair, 439
- anamorphic imaging, 249, 253, 614
- anamorphic system, 614
- high-NA, 615
- angle-resolved scattering (ARS), 281
- annulus (or ring field), 271
- antireflective coating (ARC), 413
- a-periodic multilayer coatings, 300
- aplanatic design, 255
- ArF resist polymers, 522
- Arrhenius law, 302
- asphere, 17, 27, 227, 272
- fabrication, 19, 28
- aspheric departure, 26
- aspheric surfaces, 2
- Association for Super-Advanced Electronics Technologies (ASET), 20
- astigmatic errors, 273
- astigmatism, 25
- at-wavelength inspection, 35, 37
- atomic force microscopy (AFM), 10, 275, 525
- atomic hydrogen cleaning, 390
- atomic scatter factors, 689
- attenuated phase shift mask, 461, 466
- Au-drum target, 39
- AZ PN114, 38
- ## B
- backscattered primary electron (BSE), 444
- backside conduction layer, 413
- barrier layers, 301
- beam transport system (BTS), 114
- Beer–Lambert law, 629
- Berkeley direct contrast tool (DCT), 540
- Bessel function of the first kind, 289
- BESSY, 230
- Biafore full stochastic model, 556
- Bicerano’s graph-theoretical method, 503
- bidirectional scattering distribution function (BSDF), 281–283, 285
- bipyridine ligands, 542
- bismuth oligomers, 541

- bis-phosphine palladium
 - oxalates, 543
- BL1b, beamline, 346
- BL8, beamline, 350
- blazed-grating filter, 259
- bore geometry, EQ-10195
- Boremann effect, 372
- boron carbide (B_4C), 302, 423, 455, 500
- Bossung curve, 460, 461
- bright-field image, 432
- bright-field masks, 281, 543
- bright-field signals, 434
- Bragg reflection, 370, 412
- Bragg wavelength, 23
- Bragg's law, 419
- broadband coatings, 301
- broadband mirrors, 300
- buffer gas, 401
 - specific heat capacity, 147
 - alternatives, EUV
 - transmission, 148
 - alternatives, heat
 - conductivity, 148
 - mitigation, 385–387
- C**
- CaF_2 birefringence, 74
- capping layer, 185, 305, 340, 341, 413, 423, 427, 431, 437, 443, 466
 - carbon, 338
 - ruthenium, 342, 345, 432, 457
 - SiN, 398
 - standard benchmark, 341
 - TiO_2 , 342, 343
 - ZrN, 398, 399, 401
- carbon (C), 3, 34, 302, 423
- carbon-based resists, 24
- carbon contamination, 37, 337
- carbon deposition, 336
- carbon growth rate, 350
 - for several wavelength bands, 350
- carbon K x-rays, 5
- carbon layer, 305, 336
- carbon nanotube (CNT), 455
- carbon removal, 336
- carbonaceous film, 351
- carbonaceous layer, 339
- carbonization, 336, 338, 339, 345
- carboxylate ligands, 537
- Cassegrain multilayer telescope, 33
- Cassegrain reflector, 256
- catalytic probes, 395
- Center for Plasma-Material Interactions (CMPI), 376
- centroid wavelength shift, 437
- charge-and-deflect concept, 132
- charge exchange collision, 381
- chemical mechanisms of EUV exposure, 505, 508, 517
- chemical sensitivity, 505
- chemically amplified resist (CAR), 356, 497, 505
 - non-CAR, 503, 563,
- chief ray angle (CRA), 473
- chief ray angle at object side (CRAO), 241–243, 246–248, 271–272, 610, 621
- chipmakers, leading-edge, 82
- chirp rate, 177
- chromatic vignetting, 24
- CLEARCERAM[®], 275
- clearing dose E_0 , 497
- CO_2 laser, 166, 178–179
 - amplifier, 120
 - beam diameter, 169
 - high-power, 114, 120
- coating influence on the PSD, 305
- coefficient of thermal expansion (CTE), 256, 626
- coherence time, 664
- coherent scattering microscopy (CSM), 472
- collector contamination, 370
- collector lifetime, 40, 142, 146, 219, 371, 386, 401

- colloidal graphite-coated target, 4
 computer-controlled optical surfacing, 17, 28
 computer-controlled polishing (CCP), 274
 computer-generated holographic nulls, 17, 29
 COMSOL Multiphysics[®], 396
 concave spherical mask, 7
 condenser mirror, 39
 —lifetime, 41
 contact hole (CH), 240, 443, 457, 543, 554, 557, 559, 594
 contact hole printability, simulation, 619
 contamination growth, 349, 355
 contamination rates, 345, 347, 349
 continuous slowing-down approximation (CSDA), 510
 continuous-wave source, 346
 continuum model of absorption, 549
 conversion efficiency (CE), 10, 38, 116, 120, 123, 136, 166, 182, 198, 213, 383
 cooperative research and development agreement (CRADA), 13, 59
 COSTAR correction optics, 28
 Coulombic acceleration, 376
 cracking efficiencies, 388
 critical dimension (CD), 22, 112, 597
 critical dimension uniformity (CDU), 271, 281, 598, 604, 659
 critical illumination, 13, 265
 cryogenic pellet targets, 41
 (cyclohexyl)₃Sb(O₂CH=CH₂)₂, 546
 CXRO, 197
 —website, 689
- D**
 dawn of EUVL, 8
 dark-field masks, 543
 dark-field microscopy, 432
 dark-field scanning mode, 432
 dark-field signal, 434
 debris mitigation, 38, 40, 142
 —magnetic, 150, 166, 381
 debris shields, 209
 decadic TISD, 289
 defect reduction trend of EUV mask blanks, 426
 defect signal enhancement, 438
 defect signal intensity (DSI), 433–435
 defect smoothing, 425
 Defense Advanced Research Projects Agency (DARPA), 67
 Department of Commerce (DOC), 67, 88
 Department of Defense (DOD), 67
 Department of Energy (DOE), 67
 deprotection strategy, 533
 depth-graded multilayer coatings, 300
 depth of focus (DOF), 22, 240, 461, 600, 652
 diamond grinding wheel, 28
 dibenzyl tin dibenzoate, 544
 —imaging capabilities, 544
 diffraction-limited imaging, 8
 dilatometer, 415
 Dill A parameters, 501
 Dill B parameters, 497, 501
 Dill C parameters, 497
 Director of Defense Research & Engineering (DDR&E), Office of the, 67
 discharge-produced plasma (DPP), 75, 113, 193, 207, 214, 254, 370, 422
 discrete model of absorption, 549
 discrete stochastic models, 548
 disk-shaped electrodes, 207
 disk target, 135, 170, 171
 dome target, 171
 dose-controlled EUV power, 129

- dose error, 118, 281, 598
- dose stability and control, 118, 155, 183, 215, 221
- dose tolerance, 240
- double-logarithmic PSD curve, 286
- drive laser, 110, 118, 119, 121, 123, 124
 - high-power, 126
- droplet generator (DLG), 114, 131
 - parameters, 131
 - steering system (DGSS), 154
- droplet steering, 154
- dual stage, 628
- duty cycle, 116, 119, 136, 183, 212
- DUV binary mask, 413
- DUV plasma spectra, 140
- DUV ZEISS AIMS, 309
- dynamic gas lock, 357

- E**
- E_{size}*, 542
- economic downturn, 85
- edge placement error (EPE), 604
- effective attenuation length (EAL), 351
- eight-mirror shell collector, 257
- elastic scattering, 507
- electro-optical modulation, 175
- electron-beam deposition repair, 446
- electron-beam evaporation, 304
- electron-beam-induced deposition
 - of carbon, 337
- electron-beam projection
 - lithography (EPL), 68, 84
- electron-beam repair, 442
- electron binding energies, 689, 699
- electron density, 97, 171, 395, 418
- electron ionization, 506
- electron temperature, 114, 171, 378
- electron trapping, 513
- electron travel range, 515
- electrostatic clamp, 634
- electrostatic repeller field, 40

- electrostatic wafer chuck, 15
- ellipsoid collector, 260
- ellipsoid mirror, 256, 260
- embedded phase shift mask
 - structure, 469
- energy extraction efficiency, 178
- energy overhead, 155
- energy sector analyzer (ESA), 376–377
- EMF, 195
- Engineering Test Stand (ETS), 17, 58, 110, 308, 660
- environmentally stable chemically amplified resist (ESCAR), 518–519
- EQ-10, 193
- ESA's XMM-Newton x-ray observatory, 259
- ESPRIT, 229
- etch selectivity, 465
- etch stop layer (ESL), 465–467
- etched binary mask, 464
- etched flux, 388
- étendue, 116, 118, 196, 198, 212, 255, 265, 312
- EUCLIDES, 20, 229
- EUREKA, 299
- EUV-2D, 504
- EUV beam analyzer, 210
- EUV blank multilayer requirements, 413
- EUV camera, 211
- EUV chemically amplified resist (CAR), 508
 - electron trapping, 508
 - hole-initiated, 508
 - internal excitation, 508
- EUV dual pods, 314
- EUV emission
 - position stability, 216
 - volume, 208
- EUV illuminator, 622
- EUV-induced cracking, 351
- EUV interferometry, 32

- EUV light
 - film absorbance, 504
 - incoherent sources, 113
 - EUV LLC, 2
 - risk-level definitions, 70
 - EUV mask
 - defects on, 311
 - fabrication process flow, 414
 - shadowing effect, 459
 - EUV Mask Infrastructure (EMI) consortium, 308
 - EUV multilayer, TEM image, 337
 - EUV multilayer, microstructure, 342
 - EUV optical density, 502
 - EUV optical system, 227, 241
 - resolution, 241
 - EUV pellicle, 428, 454, 635
 - guidelines and requirements, 453
 - mounting, 637
 - principle, 637
 - temperature profiles, 455
 - EUV penetration region, 667
 - EUV polarimeter, 299
 - EUV power at IF, 120, 129
 - EUV projection system, first, 605
 - EUV reflectance spectra, theoretical and experimental, 420
 - EUV reflectivity, 300
 - measurement, 395
 - EUV reflectometers, 422
 - EUV resist absorbance, 503
 - EUV scanner, optical column, 611, 614–615
 - EUV scanner, optical train, 228
 - EUV scanner ring field, 313
 - emulation, 313
 - EUV source, Sn-based, 622
 - EUV source requirements, 116
 - cleanliness, 116
 - EUV power (inband), 116
 - integrated energy stability, 116
 - size, 117
 - output, étendue, 116
 - max. solid angle input to illuminator (sr), 116
 - repetition frequency, 116
 - spectral purity, 116
 - EUV source–scanner interface, 153
 - EUV source tin consumption, 152
 - EUV source vessel, 113, 115
 - EUV spectrometer, 201
 - EUV step-and-scan system, 595
 - principle, 594
 - productivity, 595
 - EUV–visible scintillator, 211
 - EUVL exposure tool overview, 620
 - even aberrations, 625
 - Evolving nano-process Infrastructure Development Center (EIDEC), 355
 - Exitech Ltd, 232, 311
 - exposure latitude, 118, 240, 521, 528, 600, 623
 - exposure wavelength, 22, 227, 233, 369
 - extinction coefficients of materials at 13.5-nm wavelength, 453
 - extracavity modulation, 175
 - extreme-ultraviolet lithography (EUVL), 2, 3, 11, 21, 22
 - Extreme Ultraviolet Lithography System Development Association (EUVA), 20
 - EXULT project, 20, 299
- F**
- f*, 120
 - fabrication tolerance, 276
 - far-field test tool (FFTT), 138
 - Faraday cup (FC), 379
 - fast axial flow (FAF)
 - fast electrical pulse, 194
 - figure, 28, 230, 271, 272, 279, 305,
 - control, 277–278
 - correction, 274

—errors, 29, 34, 273, 275, 280, 289, 293, 305, 307
 —metrology, 276
 fast transverse flow (FTF), 121, 178
 field facet module, 622
 field of view (FOV), 309
 film quantum yield (FQY), 509
 Fizeau interferometer, 11, 19, 277
 flare, 16, 32, 236, 239, 291, 297
 —density $FD^{(n)}$, 296
 —efficiency function, 295–296
 —sources, 279
 flexible illumination, 237, 268, 609
 —modes, 623
 flexure-suspended balance masses, 627
 fluoropolymers, 502, 504
 fly’s eye integrator unit, 266
 focus offset optimization, 438
 focused ion beam (FIB), 429, 437, 446
 footprint, 209, 221
 Foucault testing, 32
 four-aspherical-mirror reflective imaging system, 26
 four-mirror EUV imaging system, 17
 fractal, 31
 fragments, number of, 173
 Fraunhofer Institute for Laser Technology (ILT), 207
 free-radical polymers, 522
 frequency-doubled Nd:YAG laser, 39
 Fresnel number, 179
 front-opening unified pod (FOUP), 634
 full-aperture interferometer, 275
 full-field production tools, 609
 full-field tools, 228, 606, 608–609
 —EUV1, 228, 234, 608
 full scanner emulation, 312
 full-time equivalent (FTE), 83

G

g-line of mercury (Hg), 5
 gain switching, 174
 gallium ions (Ga^+), 446
 gas chromatograph with a mass spectrometer (GC-MS), 354
 gas field ion source (GFIS), 446
 gas jet, 40
 gas puff targets, 41
 GC-MS with cryofocusing, 354
 glass ceramics, 275
 glass transition temperature T_g , 522, 523
 grazing-incidence collector, 255, 375
 —Wolter type, 255, 256
 grazing-incidence optical system, 15
 grazing-incidence Ru collector, nested, 219
 grazing-incidence Ru collector lifetime, 219
 grazing-incidence Ru mirror, 220

H

H_2 bubbles, 147, 400
 hafnium oxide, 535
 hafnium oxide sulfate (HafSO_x), 535
 Halbach array, 379
 Han stochastic model, 553
 Henke elemental absorption coefficients, 503
 Henke tables, 37
 hexafluorine (SF_6), 431
 Hidaka Kougaku, 11
 high-density gas clusters, 41
 High Energy Physics Laboratory, 5, 19
 high NA, 232, 241, 244, 246, 249
 —DUV ZEISS AIMS tool, 309
 —multiple-patterning extension, 639
 —QF, 613
 —scanner, 600, 619

- High Power EUV Irradiation Tool, 357
- high-power seed system (HPSS), 126
- high-precision metal replica process, 258
- high-pupil-frequency aberration, 291
- high-resolution encoder sensor, 626
- high-spatial-frequency roughness (HSFR), 17, 31, 273, 279, 305, 415
- high-volume manufacturing (HVM), 79, 94, 109, 165–167, 227, 370, 433–435
- Himeji Institute of Technology (HIT), 20
- HiNA, 232
- Hinsberg stochastic model, 553
- hole-initiated chemistry, 511
- homolysis of tin–carbon bonds, 540
- homolytic cleavage of the M-carboxylate bond, 545
- honeycomb mesh structure, 454
- horizontal/vertical (H-V) bias, 234
- hot filament hydrogen radical source, 388
- hydrogen-based cleaning, 373
- hydrogen buffer gas pressure, 144
- hydrogen etching of Sn, 388
- hydrogen implants, 401
- hydrogen penetration, 185
- hydrogen radical, 336, 358
—cleaning, 391
- hydrogen silsesquioxane (HSQ), 562
- hyperboloid reflector, 256
- I**
- ideal PSF (Airy disk), 289–293
- illumination channel, 267
- illuminator, 228, 263, 594
- illuminator pupil tuning, 269
- image contrast, 250, 430
- image optimization, 269
- image placement error (IPE), 415–416, 462, 465
- image quality, 250
- IMEC—Interuniversity Microelectronics Centre, 228
- in situ* cleaning, 40, 102, 105, 156, 371, 387
- inband EUV brightness, 198, 213
- inband EUV output power, 213
- inband EUV spectrum, 117
- inplane distortion (IPD), 430
- intensity dependence, 345–349
- intensity uniformity, 263
- interdiffusion, 301, 338
- interface roughness, 301, 424
- interferogram, 231
- interferometry-based metrology, 231
- intermediate focus (IF), 112, 153, 219, 228, 621
- internal excitation, 514
- inverse Cassegrain, 25
- ion average charge state, 171
- ion-beam figuring (IBF), 274
- ion-beam projection lithography (IPL), 68, 84
- ion-beam sputter deposition (IBD), 36, 304, 420
- ion polishing, 425
- ion spectra, 378
- ion wind, 134
- ionization rate of Sn, 173
- IR drive laser, 262
- IR-suppression grating, 262
- iridium (Ir)-coated Schwarzschild optic, 8
- isomorphic system, 614
- ITRS, 42, 60, 602
- J**
- joint development agreement (JPA), 68
- joint development program (JDP), 61

K

k_1 , k_2 , 22, 226, 597, 600
ketal protecting group, 532
ketone, 532
kinetic traces, 511
Kirchhoff mask, 463
Köhler critical-illumination system,
20, 265–267
Köhler design, 10
KrF excimer laser, 10
KrF laser-induced soft-x-ray
source, 20

L

L_4 Pd complex, 544
large-scale integration, 42
Larmor movement, 166
laser amplifier, 120
laser-assisted discharge-produced
plasma (LDP), 207
laser-induced fluorescence, 172
laser plasma source, 10
laser power, 120
laser-produced plasma (LPP), 38,
40, 109, 112, 113
—sources, 113, 115, 126, 166
laser shockwave cleaning
(LSC), 457
laser-to-droplet targeting, 155
laser-to-droplet timing, 154–155
layered synthetic microstructure
(LSM), 4
lifetime, 118
lifetime studies, 338
line-edge roughness (LER), 38, 43,
415, 539, 549, 556–557
—modeling, 671
line-edge roughness transfer
function (LTF), 660–663
linewidth roughness (LWR), 503,
526, 529, 533, 563, 569, 604
liquid-droplet target system, 20, 41
liquid metal ion source (LMIS), 446

liquid tin, 208
—bath, 207–208
—thermal conductivity, 209
lithium salt of ethylenediamine
(LiEDA), 37
lithographic resolution, 652
load mismatch, 201
local-oxidation-of-silicon
(LOCOS), 17
local critical dimension uniformity
(LCDU), 598–599, 604, 618
long-term aberration drifts, 626
longwave surface figure errors, 275
low-activation-energy system, 521
low-departure aspheric reflectors, 16
low-energy electron scattering in
solids (LESiS), 510, 516
low-étendue source, 265
low-LER dibenzyl tin complexes, 544
low-spatial-frequency roughness
(LSFR), 280
low-thermal-expansion material
(LTEM), 34, 413

M

magnetic debris mitigation, 150,
166, 381
magnetic plate, 627
magnetically levitated wafer stage, 15
magnetorheological figuring
(MRF), 274
magnetron sputtering, 304
magnification (MAG), 230,
241–243, 251
mandrels, 258
Maréchal criterion, 32, 276
Marshall Space Flight Center, 3
mask effect on high-NA
imaging, 247
mask efficiency, 250
mask error enhancement factor
(MEEF), 470
mask (reticle) handling, 636

- mask heating, 632
mask MSFR (slope error), 415
mask stage, 628
mask writing errors, 598
mass-limited target, 40, 114
master oscillator power amplifier (MOPA), 110, 114, 121, 175
—architecture, 123
—with pre-pulse, 121
mechanism for the generation of acid in CARs, 512
MEDEA+ Extreme UV Alpha Tools Integration Consortium (EXTATIC), 21
Media Lario Technologies, 259
megasonic cleaning, 418
MET5, 232, 606
metal-containing resists, 568
metal-oxide films, 535
metal-oxide model, 559–560
metal-oxide semiconductor (MOS), 12
methacrylate [$-\text{O}_2\text{CC}(\text{CH}_3)=\text{CH}_2$], 539
metrology source requirements, 198
Microelectronics Development for European Applications+ (MEDEA+), 21
micro-exposure tool (MET), 67, 228, 230, 563, 670
—image field, 228
micro-interferometers, 274
microscope, resolution limit, 226
mid-spatial-frequency roughness (MSFR), 16, 17, 32, 273, 279, 305, 415, 655
Mie scattering, 172
mirror surface errors, 655
mitigating gas, 357
Mo/Si coating at normal incidence, —peak reflectivity, 419
Mo/Si mirror reflectivity, 118, 227
Mo/Si multilayer, TEM image, 423
Mo/Si multilayer mirror
—long-term stability, 338
—planar, 211
—spherical, 211
Mo/Si stack, cross-sectional TEM image, 419
 MoSi_2 , 342
mode-locking, passive or active, 174
modeling of resist
—development, 552
—exposure, 552
—image intensity distribution, 551
—initial resist rate, 551
—post-exposure bake, 552
modulation transfer function (MTF), 660, 662–663
moiré alignment system, 15
molar metal-to-sulfate ratios, 535
molecular dynamic simulation, 558–559
Molecular Organometallic Resists for EUV (MORE), 542
mononuclear organometallic complexes, 542
Monte Carlo modeling, 510, 533
multilayer defect avoidance (MDA), 440
multilayer mirror lifetime, 373
multilayer mirror reflectivity, 374
—theoretical, 373
multilayers as Bragg reflectors, 227
multiple-epoxy-containing crosslinker, 524
multiple patterning, 226
Multivariate Poisson Propagation Model (MPPM), 675, 678
—predicted LWR and CDU terms, 680
- N**
nanomachining, 444
nanoradian, 272

- NaOH, 497
National Institute for Standards and Technology (NIST), 67, 344
Nd:YAG lasers, 208
negative chemically amplified resist
 AZ PN114, 497
negative-tone sensitivity of
 resists, 542
New Energy and Industrial
 Technology Development
 Organization (NEDO) Japan,
 179, 185
next-generation lithography
 (NGL), 64, 230
niobium oxide, 305
no master oscillator (NOMO), 121
nonlinear coupled oscillator,
 driven, 195
non-null Fizeau interferometer, 29
nonstochastic continuum models,
 548, 553, 569
normal-incidence
 —design, 136
 —collector, 375
 —ellipsoid collector, 261
 —EUV collector, 111, 114,
 137, 255
 —reflective optics, 3
 —reflectivity, 6
normalized image log slope (NILS),
 246, 264, 597, 612
Northrop Grumman, 87
novolaks, 502
NTT superconducting storage ring
 in Atsugi (Super ALIS), 13
nuclear magnetic resonance
 (NMR), 530
NuFlare Technology, Inc., 235
null corrector, 277
numerical aperture (NA), 2, 226
 —further increase, 639
NXE:3100, 608
NXE:3300B, 109, 229
 —illumination settings, 238
NXE:3350B, 109, 229, 237, 240,
 599, 609
NXE:3400B, 109, 229, 609–610
 —illumination settings, 238
- O**
obscuration impact on
 imaging, 246
odd aberrations, 625
off-axis illumination, 117, 226
off-axis Schwarzschild system, 25
Offner ring-field imaging system,
 8, 16
on-product overlay (OPO), 602–603
 —typical budget, 603
open-frame exposure, 248
open-loop power, 129
optical constants, 690
optical proximity correction
 (OPC), 234, 267, 553
optical transfer function
 (OTF), 660
optical triangulation, principle, 630
optics contamination, 335
 —summary and outlook, 358
organometallic tin dicarboxylates
 $[R_2Sn(O_2CR')_2]$, 544
organosilane monolayer film, 37
out-of-band (OOB) energy
 monitor, 210
out-of-band (OOB) light, 173
out-of-band (OOB) radiation, 138
 —power measurements,
 215, 140
out-of-band (OOB) spectrum from
 EUV plasma, 174
out-of-plane distortion, 427, 428
overhead, 120
 —time, 119
overlay errors
 —application-specific, 602
 —dedicated chuck, 602
 —matched machine, 602
 —related to customer process, 602

- oxalate ligands, 545
 oxalate loading, 542
 oxidization, 338
- P**
- PAG triphenylsulfonium tris
 (trifluoromethansulfonyl)
 methane, 511
- palladium (Pd), 258,
 342, 544
- para*-amide-styrene, 531
- paraboloid mirror, 256
- parasitic reflections, 122
- parasitic seeding, 175
- partial coherence (σ), 228, 229,
 232, 264, 623, 653, 654,
 664, 666
- patents
 —environment, 102
 —ETS and illuminator, 103–104
 —lithography, 104
 —mask, 103
 —metrology, 100
 —miscellaneous, 105
 —multilayer, 101–102
 —optics, 100–101
 —source, 104
- Paul Scherrer Institut (PSI), 536
- PdAu, 342
- PdO, 429
- peak brightness, 221
- pedestal, 175
- pedestal energy, 124–125
- pellicle-mounting structure, 456
- pellicles, 115, 450
 —CNT-based, 456
 —membrane, 452
- pentafluorobenzene-sulfonic acid
 ($C_6F_5SO_3H$, PFBS), 530
- perfluorobenzenesulfonate esters
 (3HC, 3MC, 2MC), 529
- perfluorooctane sulfonic acid
 (PFOS), 530
- periodic change relationship to
 figure change, 307
- phase defects, 35, 417, 433
 —printable, 436
- phase-measuring interferometer
 (PMI), 28
- phase shift error, 466
- phase shift mask (PSM), 429
 —relief-substrate, 657
- phase-shifting point-diffraction
 interferometer (PSPDI), 22, 30
- $Ph_3Sb(O_2CH=CH_2)_2$, 546
- $Ph_3Sb(O_2CH_3)_2$, 546
- $Ph_nM(acrylate)_2$, 545
- photo-acid generator (PAG), 355,
 504, 511, 678
 —reduction potential, 514
- photodecomposable nucleophile
 (PDN), 523
- photo-electrons, 506
- photo-ionization, 506
- photolysis mechanism, 540
- photon energies, 704
- photosensitized chemically
 amplified resist (PSCAR™), 526,
 532, 569
- photosensitizer (PS), 533
- photosensitizer precursor (PP), 532
- PHS-type CAR, 508
- physical constants, 698
- physical interactions of electrons
 with molecular species, 507
- Physikalisch-Technische
 Bundesanstalt (PTB), 298
- plasma-assisted cleaning by
 electrostatics (PACE), 457
- plasmon generation, 506
- platinum oxalates, 543
- point spread function (PSF),
 288, 663
- Poisson distribution, 548
- Poisson number, 305
- poly-4-hydroxystyrene (PHS), 512

- poly-4-methoxystyrene (PMS), 512
polybutene-1 sulfone (PBS), 37
polyhydrostyrene, 502
polymer backbone, 355
polymer-bound AAs, 531
polymerization of organic molecules, 337
polymerization olefin loading (POL), 547
poly(methyl methacrylate) (PMMA), 10, 37, 495–498
—B and C parameters, 498
—exposure sensitivity curves, 499
—spectral characteristics, 496
polyphenolic molecule, 523
polystyrene latex (PSL), 458
polyvinyl phenol polymers, 521
positive-tone palladium oxalates, 543
post-exposure bake (PEB), 498, 677
power requirement, source, 116
power spectral density (PSD), 31, 270, 284, 660–661
precision aspheres, fabrication, 22
precision-to-tolerance ratio (P/T), 276
pre-pulse (PP), 110, 154
—laser, 167
—technology, 166
pre-pulse, picosecond, 168
pre-pulse-conditioned target, 110
pressure dependence, 347–350
primary growth mechanism due to secondary electrons, 340
process window, 252–253, 270, 599
—simulation, 616
Programme Extreme UV (PREUVE), 21
projection optics, 228
projection optics box (POB), 67, 594, 606–609, 622
—heating, 632
PROLITH, 510, 559
proximity effect test patterns, 431
proximity x-ray lithography, 68, 84
PSF_{flare}, 292
pulse count modulation (PCM), 155
pulse-forming system, 194
pulse radiolysis, 510–511
pulse-shaping switch, 124
pulsed-laser deposition, 304
pulsed source, 346
pupil facet mirror, 622
pupil fill ratio, 226, 237, 264, 269, 599, 609–610, 623
- Q**
Q-switching, 175
—intracavity, 174
quantum cascade laser (QCL)
—seeder, 177
quantum cascade laser (QCL), mid-IR emitting, 176
quantum efficiency (QE), 678
quarter-wave stack, 23
quartz crystal microbalance (QCM), 388
quasi-critical illumination, 256
quasi-conventional illumination, 313
quencher, 356
- R**
radiation hardness, 338
radiation hydrodynamics simulation, 171
radiation-induced processes related to carbon contamination, 338
radical-cation hole, 505
radical flux, 388
RAVE LLC, 444
Rayleigh breakup mechanism, 133
Rayleigh criterion, 32
Rayleigh equation, 597
Rayleigh–Rice vector perturbation theory, 281, 295
Rayleigh theory of jet breakup, 132

- reactive ion etching (RIE), 396, 496
 - reflection against an absorber
 - pattern, 616
 - reflective Cook triplet, 26
 - reflective masks, 8
 - reflective multilayer coatings, 2
 - reflective triplet, 16
 - reflectivity from a MLM versus the number of bilayers, 376
 - refractive index, 226, 273, 280, 299, 302, 418, 429, 459, 467, 689
 - refractive null, 29
 - reliability tests, long-term, 217
 - repetition rate, 118
 - residual gas analyzer, 344, 353
 - residual hydrocarbons, cracking, 34
 - resists
 - bilayer, 38
 - chain-scission, 521–532
 - electron-beam, 37
 - EUV-2D, 519
 - hafnium oxide nanoparticle, 537–539
 - high-speed negative-tone, 545
 - Inpria XE151JB and XE151IB, 536
 - KRS, 520
 - MET-1K, 520
 - metal-based, 503
 - multinuclear, 542
 - negative-tone hafnium oxide nanoparticle, photomechanism, 538
 - negative-tone nonpolymeric-based EUV, 523
 - norio-based, 523
 - OFPR Novolak, 495
 - open-source (OS1), 527
 - organo-metallic
 - OSU/Inpria dehydration mechanism and photomechanism, 536
 - outgas test, 336
 - penetration depth, 7
 - sidewall profile, 24
 - soft-x-ray, 8
 - surface-imaging, 37
 - trilayer, 38
 - tri(phenyl)antimony diacrylate (JP-20), 545
 - zirconium oxide nanoparticle, 537–539
 - resist film absorption, 501
 - resist film transmission, 501
 - resist–silicon-based positive photoresist (SPP), 495
 - resolution, 22, 226
 - resolution, LER, and sensitivity (RLS) tradeoff, 526, 534
 - rhenium-tungsten (Re-W) alloy, 3
 - rhodium (Rh), 258, 305
 - right of first refusal (ROFR), 61, 62
 - ring field, 27
 - ring-shaped field, 13
 - RMS² of the roughness, 283–284
 - RMS values of PSDs, 290
 - RMS density (RMSD), 286
 - R_nM(O₂CR')₂, 545
 - Ronchi testing, 32
 - ROSAT, 259
 - rotating mechanical chopper, 40
 - Ru-capped multilayers, 343
 - Ru sputter rate, 218
 - ruthenium (Ru), 258, 305, 423
 - ruthenium oxide, 305
- S**
- SAL601, 498, 499
 - scan velocity, 628
 - scanning electron microscopy (SEM), 308
 - scanning EUV reflective microscope (SERM), 449
 - scanning transmission electron microscopy (STEM), 343

- scanning tunneling microscopy (STM), 500
- Schwarzschild camera, 10, 498, 500
- Schwarzschild imaging system, 8, 15
- Schwarzschild optics, 2, 10, 25, 311, 495
- scraper mirror, 434
- second-row elements (e.g., C, O, N, F), 535
- second-to-last mirror, 245
- secondary debris, 152
- secondary electrons, 506
- secondary-ion mass spectroscopy (SIMS), 399
- seed wavelength, 177
- SEMATECH, 67, 228
 - EUV Resist Center, 90
 - Mask Blank Development Center, 90
 - MET, 90
 - NGL Task Force, 230
- SEMI P37-0613, 412
 - substrate requirements, 415
- SEMI P38-1103, 428
- SEMI P40-1109, 428
- Semiconductor Equipment and Materials International (SEMI) standards, 96
- Semiconductor Industry Association (SIA), 67
- Semiconductor Research Corporation (SRC), 67
- SHARP, 312
 - microscope, 249
- shadowing, 610–612
- Si-capped multilayers, 343
- SiC, 342
- SiH_x, 400
- Si/Mo ML reflectivity variation as a function of wavelength, 374
- sidewall angle, 38
- silane polymers, 504
- silicide formation, 423
- silicon carbide (SiC), 423
- simulated resist image, 441
- six-degrees-of-freedom short-stroke actuator, 627
- six-mirror optical design, 272
- slab-waveguide diffusion-cooled geometry, 178–179
- small-field tools, 607
- Sn deposition at the intermediate focus (IF), 384
- S_N2 and S_N1 reactions, 531
- SnH₄, 358
- soft-x-ray projection lithography (SXPL), 7, 11
- soft-x-ray reduction lithography, 8
- Solar and Heliospheric Observatory (SOHO), 337
- solid-state laser (SSL), 169
- solid-state laser, picosecond, 168
- SORTEC, 19
- source head module, 207
- source mask optimization (SMO), 237, 269, 623
- source requirements
 - ABI, 198, 212
 - AIMS, 198, 212
 - APMI, 198, 212
 - high-power source for scanner, 116
- spatial stability, 200
- speckle pattern, 664–665
- spectral content, 117
- spectral purity filter (SPF), 259
- spectroscopic ellipsometry (SE), 346
- spherical equivalent volume diameter (SEVD), 417–418
- sputtering yields for common MLM materials, 399
- standard-mechanical-interface (SMIF), 420
 - pods, 314
- stannane (SnH₄), 144, 149, 387
- Starlith[®]3100, 228, 236, 267

- Starlith[®] 3300 wavefronts, 239
 Starlith[®] 3300/3400, 236
 statement of work (SOW), 98
 static random-access memory (SRAM) cell, 233
 stochastic continuum models, 548
 stochastic effects, 112, 549, 554, 675
 stochastic model of absorption, 549
 stochastic models, 559
 stochastic resist chemistry, 569
 Stoney equation, 305–307
 Stopping of Range of Ions in Matter (SRIM) program, 385, 389
 striae, 275
 subaperture polishing, 28
 substrate material requirements, 413
 substrate phase defects, 37
 supermirrors, 300
 surface chemistry, 341
 surface defect, 417
 surface figure, 28
 surface finish, 28
 surface interferometry, 230
 surface topography, 292
 supersonic gas cluster targets, 41
 supersonic hydrocleaning (SHC), 457, 458
 SVG Lithography, 13, 63
 synchrotron light source, 10, 39
 Synchrotron Ultraviolet Radiation Facility (SURF), 197
- T**
t-butyl trifluoromethacrylate, 522
 T configuration, 110
 Tagawa/Kowaza modeling, 557–558
 Tamaru's redeposition coefficient, 396
 TaN absorber layer, 429
 target density, 136
 target shape, 136
 TaSiN, 431
 telecentricity, 10, 25, 249, 265, 473, 612
 temporal stability, 200
 tetrahydrofuron, 511
 thermal instability, 424
 thermal load, 116, 254, 262, 303, 632
 thermal stability of EUV multilayers, 302
 Thomson scattering, 171
 three-aspherical-mirror ring-field imaging system, 16, 20
 through-focus compensation repair, 442
 throughput, 22, 43, 115, 116, 595, 609–610, 614–615
 tin (Sn)
 —circulation modules, 208
 —cleaning rate, 149
 —cleaning technique, 142
 —clusters, mechanism of photolysis, 540
 —deposition rate, 184
 —droplets, 130
 —management inside the vessel, 151
 —removal from the vessel, 152–153
 tin-ion stopping power, 143
 tin jet breakup, 132
 tin-oxo cages, 539
 tin-oxo cluster
 [(*n*-BuSn)₁₂O₁₄(OH)₆]
 (p-CH₃C₆H₄SO₃)₂, 540
 tin-oxo cluster ([*(R*Sn)₁₂O₁₄(OH)₆]
 X₂, 539
 tin plasma, optimum ion density, 169
 Tinsley Laboratories, 11, 68
 TiO₂, 342
 TIS density (TISD), 286, 294

- TIS values of PSDs, 290
titanium dioxide, 305
TMAH (0.26 N tetramethylammonium hydroxide), 498, 522
TMAH-developable system, 524
toroidal mirrors, 10
total electron yield (TEY), 509–510, 513
total integrated scatter (TIS), 280, 285, 303, 655
total wavefront error, 625
transition-metal oxalates, 542
transmission image sensor, 631
transmission of 10-nm-thick Sn layer, 145
transmission mask, 10, 231
transverse flow of CO₂ gas, fast, 121
triflic acid (CF₃SO₃H or TfOH), 530
trifluoromethyl (-CF₃) group, 529
trigger-body design, 530
Trumpf TruFlow laser series, 178
—amplifiers, 121
TRW Inc., 68
tungsten-carbon ML, 5
turning mirrors, 119
turnover numbers, 546
two-aspherical-mirror imaging system, 10, 12, 13, 19
two-mirror illumination system, 10
- U**
ULE[®], 275
Ultratech, 68
ultraviolet cleaning, 459
uniformity correction module (Unicom), 624
United States Advanced Lithography (USAL), 63
U.S. National EUV Lithography Program, 13, 18
UV-Vis-IR absorbance, 511
- V**
vacuum vessel, 114
Veeco Instruments, 68
—low-defect-deposition ML tool, 37
Virtual National Laboratory (VNL), 61
—Resource Development Center (RDC), 87
volume sensitivity, 497
—parameter, 505
- W**
wafer heating, 632
wafer load sequence, 634
wafer stage, 627
wafer throughput model, 115
wafer-to-wafer heat exchange, 119
wafer topology, 630
wafers, cumulative number of exposed, 638
wall angles, 499
wavefront aberration, 271
wavefront error, 14, 273, 669
—aberration-driven, 273
—total system, 32
wavefront metrology, 20, 630
wavelength dependence, 350–351
wavelength reduction, 639
wet etchability, 466
white-light interferometry, 17
white papers, 72
witness sample, 355
Wolter, Hans, 255
Wolter collector, 255, 266
Wolter type-1 system, 256–257
Wolter–Schwarzschild design, 256
- X**
xMT, 524
x-ray diffraction (XRD), 422
x-ray fluorescence, 218

- x-ray photoelectron spectroscopy (XPS), 343
x-ray proximity lithography (XPL), 5, 12
x-ray reduction lithography, 5
xenon plasma, 195
- Y**
YAG-laser-driven LPP, 214
yttria-stabilized zirconia, 342
- Z**
Z-parameter, 527–528, 563
Z-pinch, 193
Zernike, Fritz, Jr., 13
Zernike coefficients, 236
Zernike polynomials, 236, 625
zero-crossing temperature (ZCT), 275, 626
ZERODUR[®], 3, 230, 275
zero-valent palladium-phosphine complexes, 544
zirconium (Zr) foils, 196
zirconium dioxide, 305
zirconium oxide sulfate (ZircSO_x), 535
zone plate, 8, 311, 434, 449
Zr-coated Si photodiode, 210
ZrH_x, 400
ZrN, 400
Zr/Si₃N₄ filter, 211